
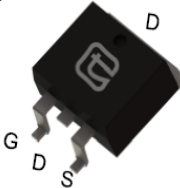

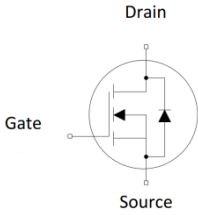


**85V N-Channel Trench MOSFET(Preliminary)**

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>● Trench Power Technology</li> <li>● Low <math>R_{DS(ON)}</math></li> <li>● Low Gate Charge</li> <li>● Optimized for fast-switching Applications</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>● Synchronous Rectification in DC/DC and AC/DC Converters</li> <li>● Isolated DC/DC Converters in Telecom and Industrial</li> </ul>	<p><b>Product Summary</b></p> <p><math>V_{DS}</math> 85V</p> <p><math>I_D</math> (at <math>V_{GS}=10V</math>) 105A</p> <p><math>R_{DS(ON)}</math> (at <math>V_{GS}=10V</math>) &lt; 8.5m<math>\Omega</math></p> <p>100% UIS Tested</p> 
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<p><b>TO-263</b></p> 	<p><b>TO-220</b></p> 		
<b>Device</b>	<b>Package</b>	<b>Form</b>	<b>Marking</b>
TTB105N08A	TO-263	Tape & Reel	105N08A
TTP105N08A	TO-220	Tube	105N08A

<b>Absolute Maximum Ratings (<math>T_A = 25^\circ\text{C}</math> unless otherwise noted)</b>			
Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	85	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>B</sup>	$T_C = 25^\circ\text{C}$	105	A
	$T_C = 100^\circ\text{C}$	73	
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	315	A
Avalanche Current <sup>A</sup>	$I_{AS}$	47	A
Single Pulse Avalanche Energy $L = 0.3\text{mH}$ <sup>A</sup>	$E_{AS}$	331	mJ
Power Dissipation <sup>C</sup>	$T_C = 25^\circ\text{C}$	195	W
	$T_C = 100^\circ\text{C}$	97	W
Operating Junction and Storage Temperature Range	$T_J, T_{SGT}$	-55 to 175	$^\circ\text{C}$

<b>Thermal Resistance</b>			
Parameter	Symbol	Maximum	Units
Thermal Resistance, Junction-to-Case	$R_{thJC}$	0.77	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient			
	$R_{thJA}$	100	



Electrical Characteristics( $T_J = 25^\circ\text{C}$ unless otherwise noted)							
Symbol	Parameter	Conditions	Value			Units	
			Min	Typ	Max		
<b>STATIC PARAMETERS</b>							
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	85	--	--	V	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 85\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$	--	--	1	$\mu\text{A}$
			$T_J = 100^\circ\text{C}$	--	--	25	
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	--	--	$\pm 100$	nA	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2	3	4	V	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}, I_D = 30\text{A}$	--	7.1	8.5	m $\Omega$	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 20\text{A}$	80	--	--	S	
$V_{SD}$	Diode Forward Voltage	$I_S = 20\text{A}, V_{GS} = 0\text{V}$	--	--	1	V	
$I_S$	Maximum Body-Diode Continuous Current <sup>B</sup>		--	--	105	A	
<b>DYNAMIC PARAMETERS</b>							
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 40\text{V}, f = 1\text{MHz}$	--	6033	--	$\text{pF}$	
$C_{oss}$	Output Capacitance		--	285	--		
$C_{rss}$	Reverse Transfer Capacitance		--	247	--		
<b>SWITCHING PARAMETERS</b>							
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 40\text{V}, I_D = 20\text{A}$	--	105	--	nC	
$Q_{gs}$	Gate Source Charge		--	33	--		
$Q_{gd}$	Gate Drain Charge		--	22	--		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 40\text{V}, I_D = 20\text{A}, R_G = 2.5\Omega$	--	24	--	ns	
$t_r$	Turn-On Rise Time		--	19	--		
$T_{D(off)}$	Turn-Off Delay Time		--	70	--		
$t_f$	Turn-Off Fall Time		--	30	--		
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$	--	37	--	ns	
$Q_{rr}$	Body Diode Reverse Recovery Charge		--	58	--	nC	

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation  $P_D$  is based on  $T_{J(MAX)} = 175^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

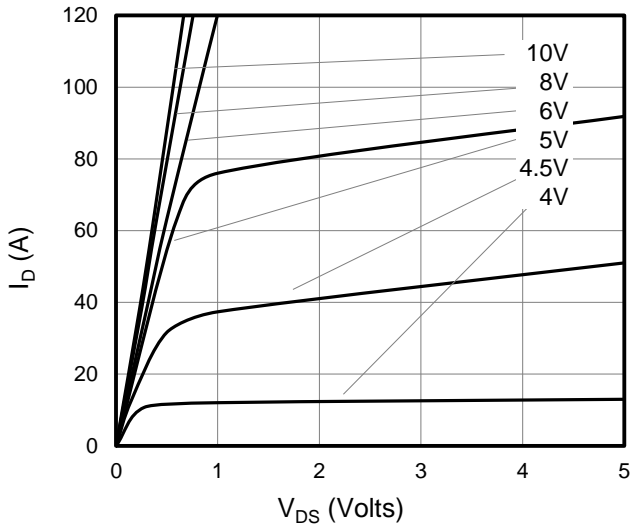


Figure 1: On-Region Characteristics

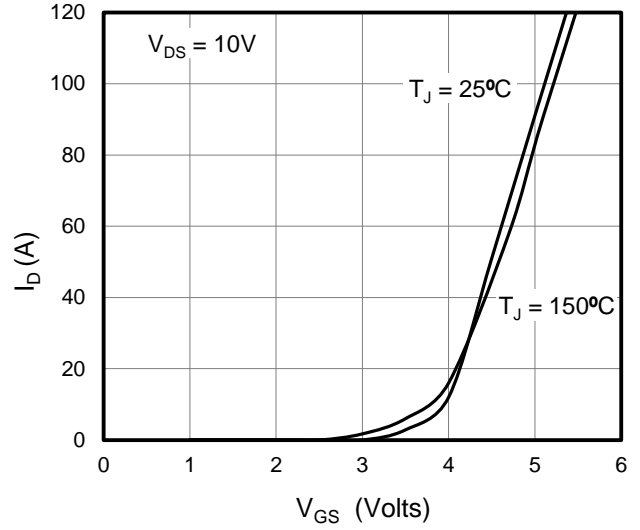


Figure 2: Transfer Characteristics

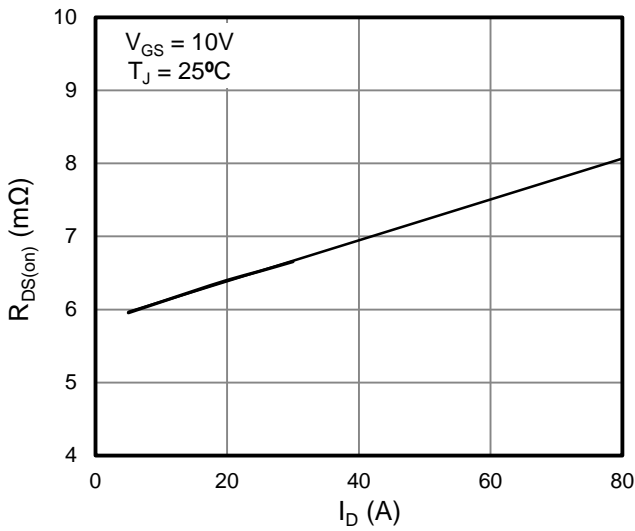


Figure 3: On-Resistance vs. Drain Current

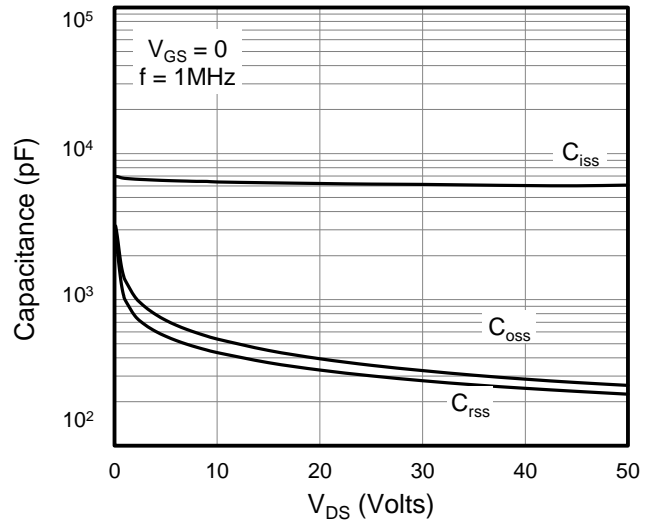


Figure 4: Capacitance Characteristics

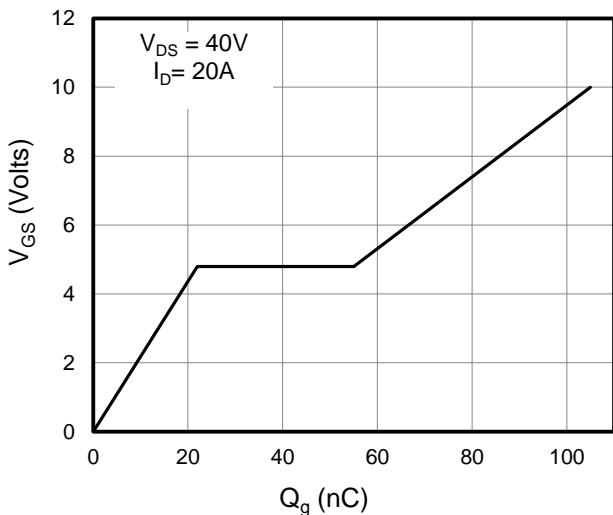


Figure 5: Gate Charge Characteristics

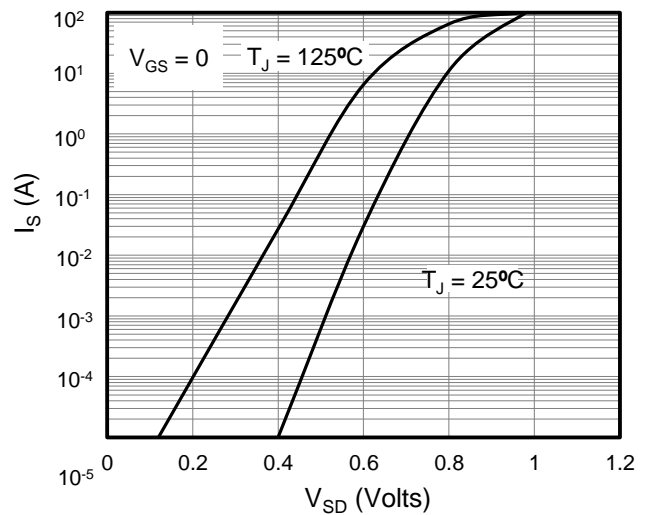


Figure 6: Body Diode Forward Voltage



Typical Characteristics  $T_J = 25^{\circ}\text{C}$ , unless otherwise noted

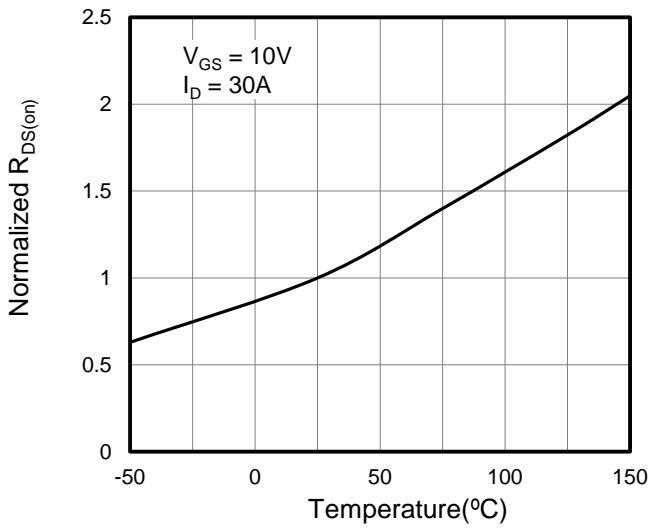


Figure 7: On-Resistance vs. Junction Temperature

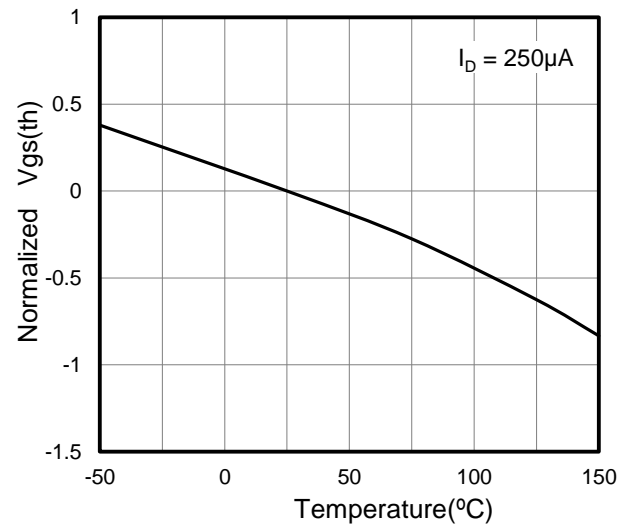


Figure 8:  $V_{GS(th)}$  vs. Junction Temperature

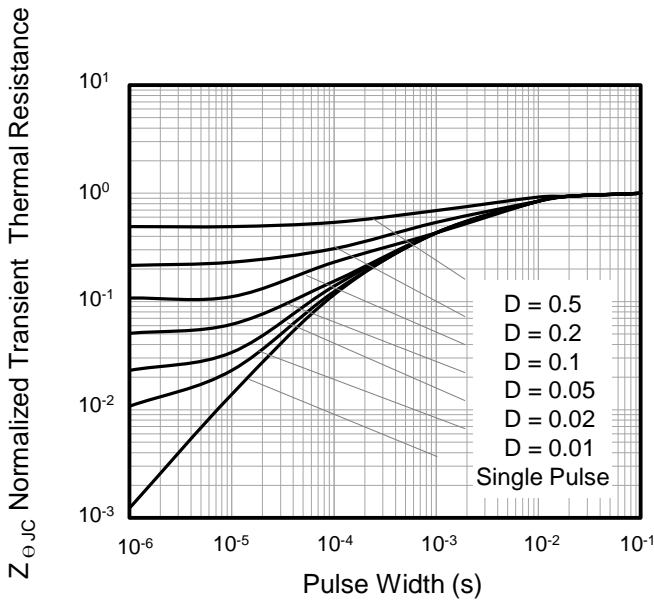


Figure 9: Normalized Transient Thermal Resistance

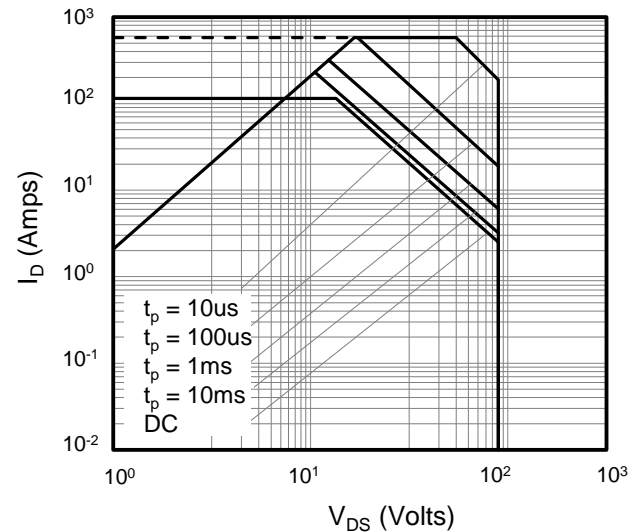


Figure 10: Safe Operating Area



Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

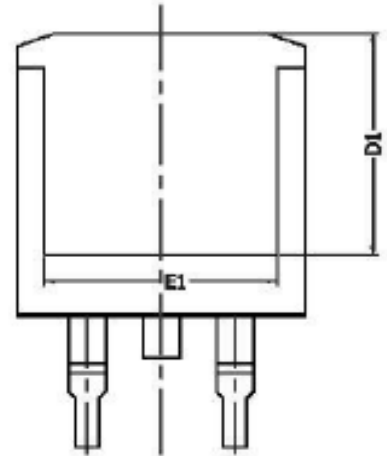
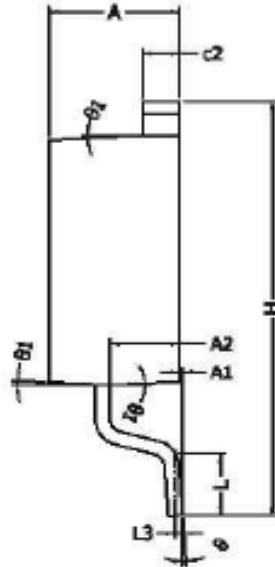
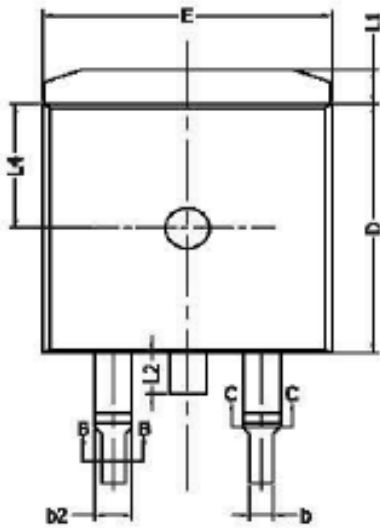


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





### TO-263(集佳)



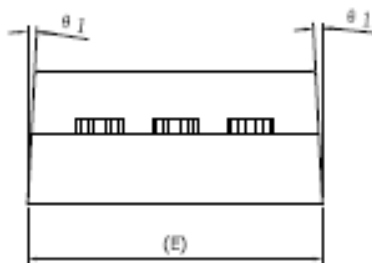
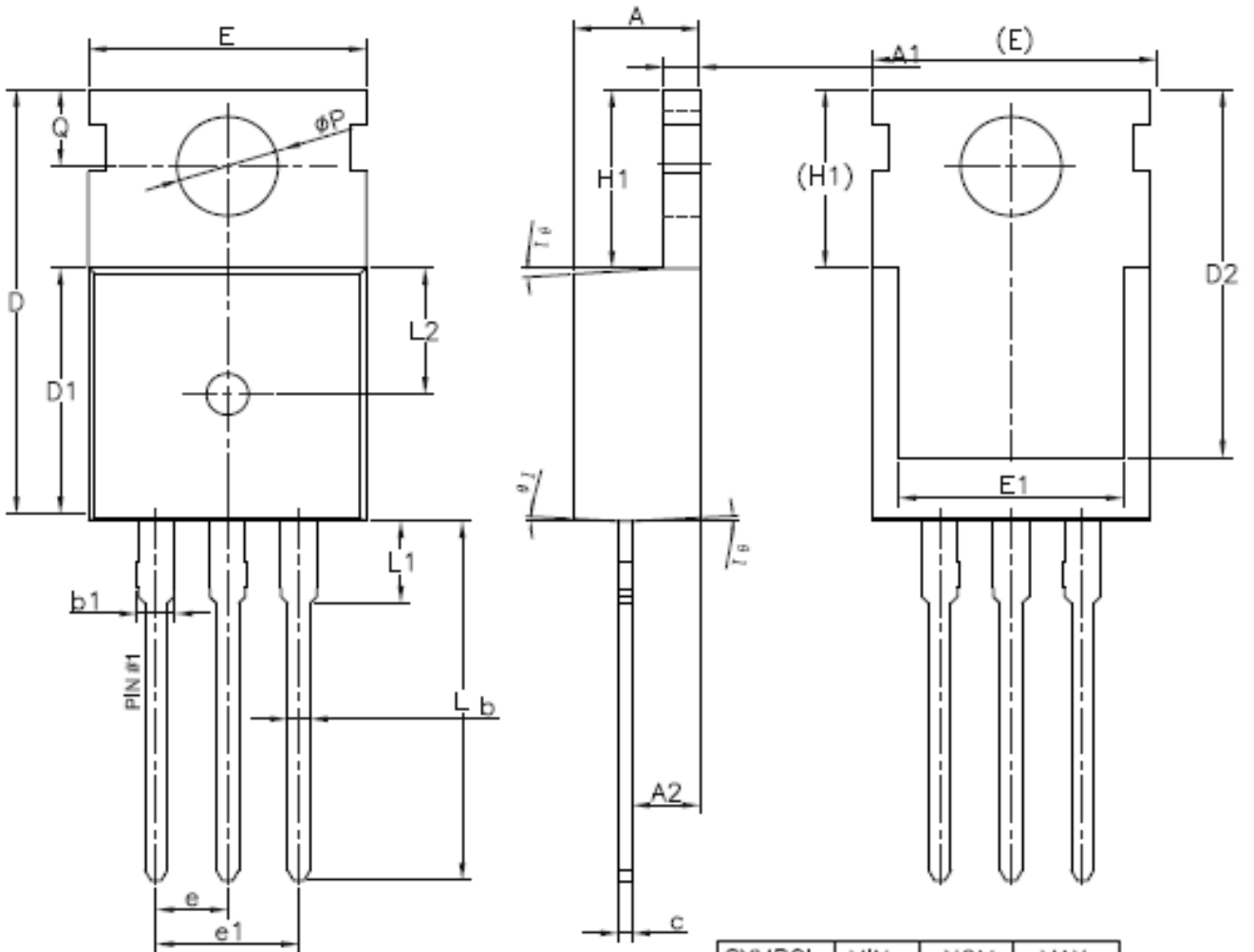
COMMON DIMENSIONS  
(UNITS OF MEASURE -MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	---	0.89
b1	0.75	0.80	0.85
b2	1.23	---	1.37
b3	1.22	1.27	1.32
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	---	---
E	9.80	9.90	10.00
E1	7.80	---	---
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	---	---	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	---	8°
θ1	1°	3°	5°





TO-220(集佳)



SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	-	0.90
b1	1.27	-	1.40
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	-	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.54BSC		
e1	5.08BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	-	-	3.50
L2	4.60REF		
$\phi P$	3.55	3.60	3.65
Q	2.73	-	2.87
$\theta_1$	1°	3°	5°



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